

VERSION WITH MARKINGS TO SHOW CHANGES MADE

Claim 1 has been amended as follows:

1.(Amended) A method of manufacturing a semiconductor device, comprising the steps of:

~~{providing a semiconductor substrate in which a cell region and a peripheral circuit region are defined;}~~

forming a patterned tunnel oxide film, a floating gate electrode, a dielectric film, and a control gate electrode in ~~{said}~~ a cell region ~~{forming a gate electrode in said peripheral circuit region}~~ of a semiconductor substrate;

forming a gate electrode in ~~{said}~~ a peripheral circuit region of the semiconductor substrate;

removing an exposed portion of a device isolation film in ~~{said}~~ the cell region by ~~{means of}~~ a ~~{self-align}~~ self-align source etch process;

forming a first capping layer and a second capping layer on the ~~{entire structure}~~ semiconductor substrate;

performing a ~~{self-align}~~ self-align source annealing process for ~~{said}~~ the cell region;

forming a source and drain junction in ~~{said}~~ the cell region ~~{and};~~

forming a low concentration source and drain junction in ~~{said}~~ the peripheral circuit region;

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forming a gate spacer in ~~{said}~~ the peripheral circuit region; and

forming a high concentration source and drain junction in ~~{said}~~ the peripheral circuit region.

Claim 2 has been amended as follows:

2.(Amended) The method ~~{of manufacturing a semiconductor device}~~ according to claim 1, wherein ~~{said first capping layer is formed in thickness of 100—200 Å}~~ a thickness of the first capping layer is 100-200Å.

Claim 3 has been amended as follows:

3.(Amended) The method ~~{of manufacturing a semiconductor device}~~ according to claim 1, wherein ~~{said second capping layer is formed in thickness of 50—150 Å}~~ a thickness of the second capping layer is 50-150Å.

Claim 4 has been amended as follows:

4.(Amended) The method ~~{of manufacturing a semiconductor device}~~ according to claim 1, wherein ~~{said}~~ the gate spacer is formed of ~~{said}~~ the first capping layer~~{,}~~, ~~{said}~~ the second capping layer~~{,}~~ and an oxide film ~~{for a spacer in a way that an oxide film for a spacer is formed on said second capping layer and said oxide film for a spacer and said second capping layer are then sequentially etched}~~ by a blanket etch process.

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Claim 5 has been amended as follows:

5.(Amended) The method ~~{of manufacturing a semiconductor device}~~ according to claim 4, wherein ~~{said oxide film for a spacer is formed in thickness of 1200—1600 Å}~~ a thickness of the oxide film is 1200-1600Å.

Claim 6 has been amended as follows:

6.(Amended) The method ~~{of manufacturing a semiconductor device}~~ according to claim 4, wherein ~~{said}~~ the oxide film ~~{for a spacer}~~ and ~~{said}~~ the first capping layer are etched through ~~{the mediation}~~ to lateral portions of ~~{said}~~ the second capping layer to form a screen oxide film.

Claim 7 has been amended as follows:

7.(Amended) The method ~~{of manufacturing a semiconductor device}~~ according to claim 1, wherein ~~{said}~~ the source and drain junction in ~~{said}~~ the cell region is formed by using ~~{said}~~ the first capping layer and ~~{said}~~ the second capping layer as an ion implantation screen oxide film.

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Claim 8 has been amended as follows:

8.(Amended) The method ~~{of manufacturing a semiconductor device}~~ according to claim 1, wherein ~~{said}~~ the low concentration source and drain junction in ~~{said}~~ the peripheral circuit region is formed by using ~~{said}~~ the first capping layer and ~~{said}~~ the second capping layer as an ion implantation screen oxide film.

Claim 9 has been amended as follows:

9.(Amended) The method ~~{of manufacturing a semiconductor device}~~ according to claim 1, wherein ~~{said}~~ the high concentration source and drain junction in ~~{said}~~ the peripheral circuit region is formed by using a lateral portion of ~~{said}~~ the first capping layer etched ~~{by a given thickness}~~ as an ion implantation screen oxide film.

Claim 10 has been amended as follows:

10.(Amended) The method ~~{of manufacturing a semiconductor device}~~ according to claim 1, wherein ~~{said}~~ the first capping and ~~{said}~~ the second capping layer ~~{functions to}~~ prohibit formation of a local bird's beak of ~~{said}~~ the dielectric film formed between ~~{said}~~ the floating gate electrode and ~~{said}~~ the control gate electrode.

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